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Form PTO-1449		ATTY DOCKET NO. 10932-US	SERIAL NO.
U.S. Department of Commerce Patent and Trademark Office		APPLICANT	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Luc OUELLET et al.	
		FILING DATE	GROUP

U.S. PATENT DOCUMENTS

*Exam. Inti.		Document Number	Date	Name	Class	Sub Class	Filing Date if Appropriate

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub Class	Translation
							Yes
							No

OTHER DOCUMENTS (Including Author, title, Date, Pertinent Pages, Etc.)

WA		D.K.W. Lam, "Low temperature plasma chemical vapor deposition of silicon oxynitride thin-film waveguides", Applied Optics, Vol. 23, No. 16, August 15, 1984, pp, 2744-2746.
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WA		K. Worhoff et al., "Plasma enhanced chemical vapor deposition silicon oxynitride optimized for application in integrated optics", Sensor and Actuators, 74, 1999, pp. 9-12.

EXAMINER	<i>W.M.</i>	DATE CONSIDERED	<i>10/4/03</i>
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<i>WA</i>		A.J. Kenyon et al., "A luminescence study of silicon-rich silica and rare-earth doped silicon-rich silica", Electrochemical Society Proceedings Vol. 91-11, pp. 304-318.						
		M. Hoffmann et al., "Low temperature, nitrogen doped waveguides on silicon with small core dimensions fabricated by PECVD/RIE", Waveguide Technology, WeC2, pp.299-301.						
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		A. Durandet et al., "Silica buried channel waveguides fabricated at low temperature using PECVD", Electronics Letters, Vol. 32, No. 4, February 15, 1996, pp.326-327.						
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<i>WA</i>		S. Valette, "State of the art of integrated optics technology at LETI for achieving passive optical components", Journal of Modern Optics, Vol. 35, No. 6, 1998, pp. 993-1005.						
EXAMINER	<i>WA MA</i>			DATE CONSIDERED 10/16/03				

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<i>WA</i>		G. Grand et al., "Low-Loss PECVD Silica Channel Waveguides for Optical Communications", Electronic Letters, Vol. 26, No. 25, December 6 1990, pp. 2135-21-37.					
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EXAMINER	<i>Wa Mart</i>			DATE CONSIDERED	<i>10/16/03</i>		
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TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))		Docket No. 10932-US
In Re Application Of: Luc OUELLET, et al.		
Serial No. 09/833,711	Filing Date 13 April 2001	Examiner Group Art Unit 2874
Title: OPTICAL QUALITY SILICA FILMS		
<p>Address to: Assistant Commissioner for Patents Washington, D.C. 20231</p> <p style="text-align: center;">37 CFR 1.97 (b)</p> <p>1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first Office Action on the merits, whichever event occurs last.</p> <p style="text-align: center;">37 CFR 1.97 (c)</p> <p>2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after three months of the filing of a national application, or the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or after the mailing date of a first Office Action on the merits, whichever occurred last but before the mailing date of either:</p> <ol style="list-style-type: none">1. a Final Action under 37 CFR 1.113, or2. a Notice of Allowance under 37 CFR 1.311, <p>whichever occurs first.</p> <p>Also submitted herewith is:</p> <p><input type="checkbox"/> a certification as specified in 37 CFR 1.97(e);</p> <p style="text-align: center;">OR</p> <p><input type="checkbox"/> the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under 37 CFR 1.97(c).</p>		

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Docket No.
10932-US

In Re Application Of: Luc OUELLET, et al.

Serial No.	Filing Date	Examiner	Group Art Unit
09/833,711	13 April 2001		2874

Title: OPTICAL QUALITY SILICA FILMS

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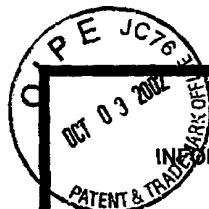
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